

Features

- High Density Cell Design for Ultra Low R_{DS(on)}
- · Fully Characterized Avalanche Voltage and Current
- · Excellent Package for Good Heat Dissipation
- · Moisture Sensitivity Level 1
- Halogen Free."Green"Device(Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

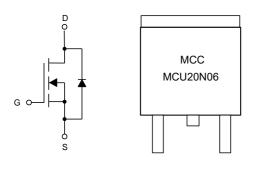
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 60°C/W Junction to Ambient^(Note2)
- Thermal Resistance: 3.1°C/W Junction to Case

Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Volltage		V _{GS}	±20	V	
Continuous Drain Current	T _C =25°C		20	Α	
	T _C =100°C	l _D	12.6		
Pulsed Drain Current (Note3)		I _{DM}	60	Α	
Total Power Dissipation ^(Note4)		P _D	40	W	
Single Pulse Avalanche Energy (Note 5)		E _{AS}	30	mJ	

Note:

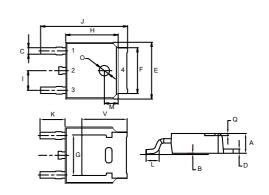
- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. P_D is based on max. junction temperature, using junction-case thermal resistance.
- 5. T_J =25°C, V_{DD} =40V, R_G =25 Ω , L=0.5mH.

=bhYfbU Gffi Wfi fY UbX A Uf_]b[7cXY



N-CHANNEL MOSFET

DPAK(TO-252)



- Gate
- 2,4. Drain
 - 3. Source

DIMENSIONS					
DIM INCHES		MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.087	0.094	2.20	2.40	
В	0.000	0.005	0.00	0.13	
С	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
Е	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
Н	0.236	0.244	6.00	6.20	
ı	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
M	0.063		1.60		TYP.
0	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.

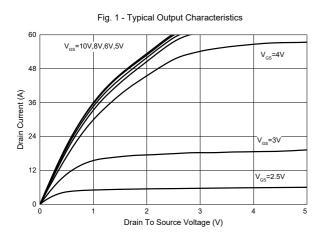


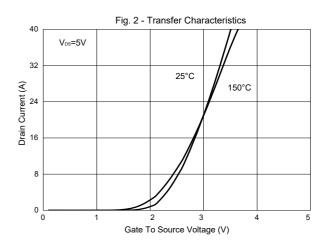
Electrical Characteristics @ 25°C (Unless Otherwise Specified)

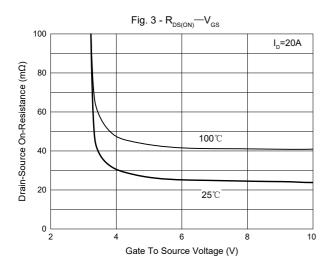
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} =0V, I_{D} =250 μ A	60			V	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1	1.5	3	V	
Drain-Source On-Resistance	_	V _{GS} =10V, I _D =20A		23	45	m-0	
	R _{DS(on)}	V _{GS} =4.5V, I _D =10A	25 4		47	– mΩ	
Gate Resistance	R_{g}	F=1 MHz, Open drain		1.6		Ω	
Diode Characteristics			'				
Continuous Body Diode Current	Is				20	Α	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =20A			1.2	V	
Reverse Recovery Time	t _{rr}	1 = 20.0 d1 /d+= 10.0 0 /u.c		23.5		ns	
Reverse Recovery Charge	Q _{rr}	I _F =20A, dI _F /dt=100A/μs		17.5		nC	
Dynamic Characteristics			<u>'</u>				
Input Capacitance	C _{iss}			1117		pF	
Output Capacitance	C _{oss}	V_{DS} =30V, V_{GS} =0V,f=1MHz		69			
Reverse Transfer Capacitance	C _{rss}			56			
Total Gate Charge	Q_g			24.5			
Gate-Source Charge	Q_{gs}	V _{DS} =48V,V _{GS} =10V,I _D =15A		2.8		nC	
Gate-Drain Charge	Q_{gd}			6.3			
Turn-On Delay Time	t _{d(on)}			6.4			
Turn-On Rise Time	t _r	V _{DD} =30V, V _{GS} =10V,		3.4			
Turn-Off Delay Time	t _{d(off)}	I_{DS} =2A, R_{G} =3 Ω		24.5		ns	
Turn-Off Fall Time	t _f			4.6			

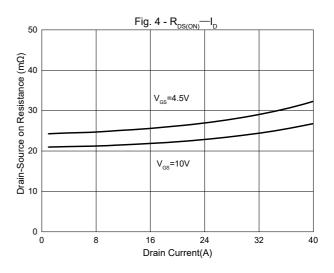


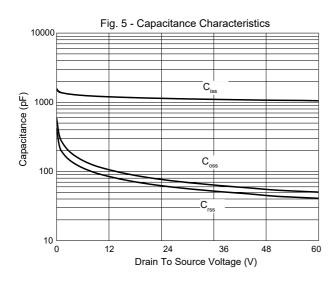
Curve Characteristics

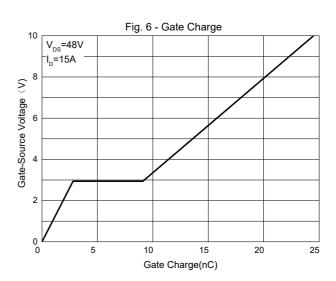






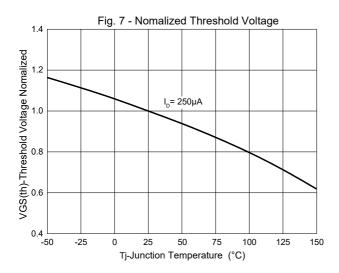


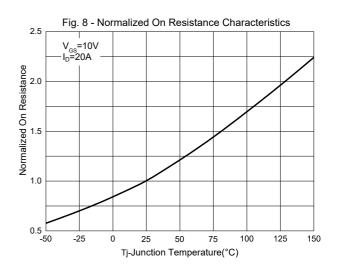


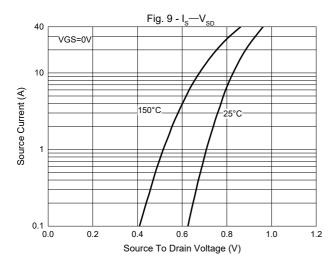


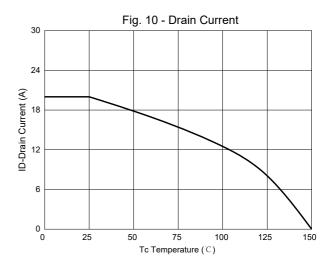


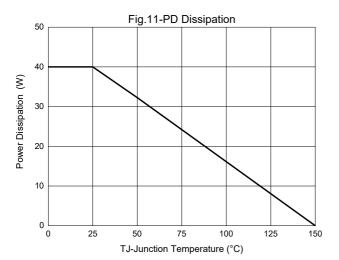
Curve Characteristics





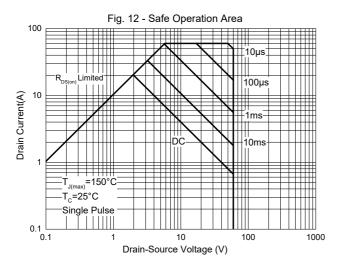


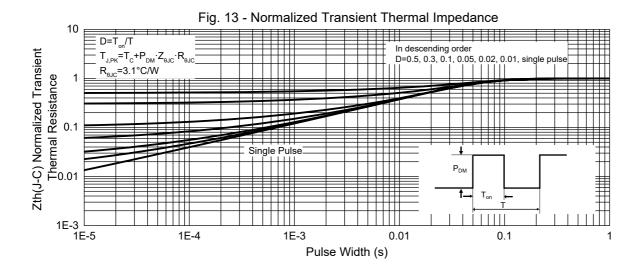






Curve Characteristics







Ordering Information

Device	Packing	
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel	

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